

FMC2122LN-03

Ku, K-Band Power GaAs Modules

ABSOLUTE MAXIMUM RATINGS (Ambient Temperature Ta = 25°C)

Parameter	Symbol	Rating	Unit
DC Input Voltage	V _{DD}	10	V
DC Input Voltage	V _{GG}	-7	V
Input Power	P _{in}	3	dBm.
Storage Temperature	T _{stg}	-55 to +125	°C
Operating Case Temperature	T _{op}	-55 to +85	°C

Fujitsu recommends the following conditions for the reliable operation of GaAs modules:

1. The drain operating voltage (V_{DD}) should not exceed 8 volts.
2. The gate operating voltage (V_{GG}) should not exceed -5 volts.

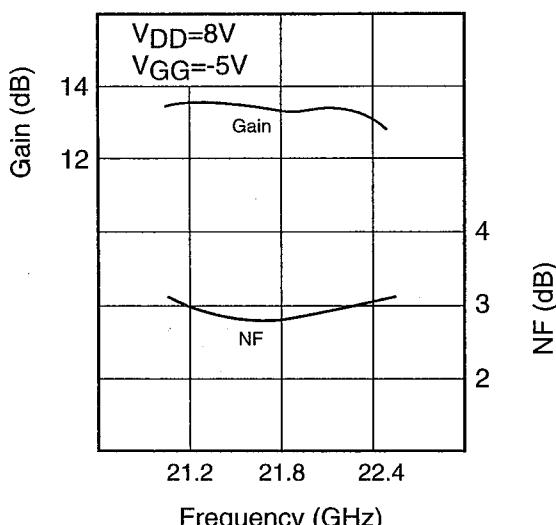
ELECTRICAL CHARACTERISTICS (Case Temperature T_c = 25°C)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Frequency Range	f		21.2 ~ 22.4			GHz
Output Power at 1dB G.C.P.	P _{1dB}	V _{DD} = 8V V _{GG} = -5V f = 21.2 ~ 22.4 GHz	11.0	12.0	-	dBm
Power Gain at 1 dB G.C.P.	G _{1dB}		11.0	12.0	-	dB
Noise Figure	NF		-	3.0	4.0	dB
Gain Flatness	ΔG	V _{DD} = 8V V _{GG} = -5V P _{in} = -15dBm f = 21.2 ~ 22.4 GHz	-	1.0	-	dB
Input VSWR	VSWR _i		-	3.0:1	-	-
Output VSWR	VSWR _o		-	2.5:1	-	-
DC Input Current	I _D		-	40	70	mA
DC Input Current	I _G	V _{DD} = 8V V _{GG} = -5V	-	10	15	mA

CASE STYLE: GJ

G.C.P.: Gain Compression Point

GAIN & NF vs. FREQUENCY



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